

a 2020 0054

The invention relates to optoelectronics, in particular to infrared radiation photodetectors.

The infrared radiation photodetector comprises a GaAs nanowire and metal contacts. At the same time, the nanowire is made by anodizing a GaAs wafer, and at the ends of the nanowire are formed ohmic Cr/Au contacts by deposition using laser beam lithography.

Claims: 1

Fig.: 4